- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V<sub>OLP</sub> (Output Ground Bounce)
   <0.8 V at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C
- Typical V<sub>OHV</sub> (Output V<sub>OH</sub> Undershoot) >2 V at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C
- I<sub>off</sub> Supports Partial-Power-Down Mode Operation
- Supports 5-V V<sub>CC</sub> Operation
- Package Options Include Plastic Thin Shrink Small-Outline (DCT, DCU) Packages

#### 

**DCT OR DCU PACKAGE** 

#### description

This dual buffer/line driver is designed for 1.65-V to 5.5-V V<sub>CC</sub> operation.

The SN74LVC2G241 is designed specifically to improve both the performance and density of 3-state memory-address drivers, clock drivers, and bus-oriented receivers and transmitters.

The SN74LVC2G241 is organized as two 1-bit line drivers with separate output-enable ( $1\overline{OE}$ , 2OE) inputs. When  $1\overline{OE}$  is low or 2OE is high, the device passes data from the A inputs to the Y outputs. When  $1\overline{OE}$  is high or 2OE is low, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking or the current-sourcing capability of the driver.

This device is fully specified for partial-power-down applications using I<sub>off</sub>. The I<sub>off</sub> circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The SN74LVC2G241 is characterized for operation from -40°C to 85°C.

#### **FUNCTION TABLES**

INPU	JTS	OUTPUT			
10E	1A	1Y			
L	Н	Н			
L	L	L			
Н	Χ	Z			

INP	JTS	OUTPUT
20E	2A	2Y
Н	Н	Н
Н	L	L
L	Χ	Z

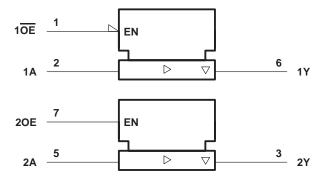


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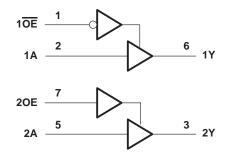


#### logic symbol<sup>†</sup>



<sup>&</sup>lt;sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

#### logic diagram (positive logic)



#### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V <sub>CC</sub>	–0.5 V to 6.5 V
Input voltage range, V <sub>I</sub> (see Note 1)	–0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V	O
(see Note 1)	–0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, VO	
(see Notes 1 and 2)	0.5 V to V <sub>CC</sub> + 0.5 V
Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0)	
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0)	–50 mA
Continuous output current, I <sub>O</sub>	±50 mA
Continuous current through V <sub>CC</sub> or GND	±100 mA
Package thermal impedance, $\theta_{JA}$ (see Note 3): DCT package	296°C/W
DCU package	329°C/W
Storage temperature range, T <sub>Stq</sub>	–65°C to 150°C

<sup>\$</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

- 2. The value of V<sub>CC</sub> is provided in the recommended operating conditions table.
- 3. The package thermal impedance is calculated in accordance with JESD 51.



# PRODUCT PREVIEW

#### recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
V/00	Supply voltage	Operating	1.65	5.5	V	
VIH H	Supply voltage	Data retention only	1.5		V	
VIH  VIL  VI VO  IOH		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65 × V <sub>CC</sub>			
	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
۷IH	r light-level input voltage	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	2		ľ	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	1.65 5.5 1.5 0.65 × V <sub>CC</sub> 1.7			
VIH H		V <sub>CC</sub> = 1.65 V to 1.95 V		0.35 × V <sub>CC</sub>		
٧/	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V	
VIH His	Low-level input voltage	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		0.8		
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		$0.3 \times V_{CC}$		
٧ <sub>I</sub>	Input voltage		0	5.5	V	
٧o	Output voltage		0	Vcc	V	
		V <sub>CC</sub> = 1.65 V		-4		
VIH VIL VI VO IOH		V <sub>CC</sub> = 2.3 V		-8		
	High-level output current	VCC = 3 V		-16	mA	
		vCC = 3 v		-24		
		V <sub>CC</sub> = 4.5 V		1.65 5.5  1.5  1.7  2  7 × VCC  0.35 × VCC  0.7  0.8  0.3 × VCC  0 5.5  0 VCC  -4  -8  -16  -24  -32  4  8  16  24  32  20		
		V <sub>CC</sub> = 1.65 V		4		
		V <sub>CC</sub> = 2.3 V		8		
$I_{OL}$	Low-level output current	Voc = 3 V		16	mA	
		vCC = 3 v		24		
		V <sub>CC</sub> = 4.5 V	CC = 1.65  V $CC = 2.3  V$ $CC = 3  V$ $CC = 4.5  V$ $CC = 4.5  V$ $CC = 4.5  V$ $CC = 4.5  V$	32		
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20		
$\Delta t/\Delta v$	Input transition rise or fall rate	Input transition rise or fall rate $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V	
	$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$			5		
TA	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

## PRODUCT PREVIEW

#### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PA	RAMETER	TEST CO	ONDITIONS	Vcc	MIN	TYP†	MAX	UNIT	
		I <sub>OH</sub> = -100 μA		1.65 V to 5.5 V	V <sub>CC</sub> -0.1				
١.,		I <sub>OH</sub> = -100 μA		,,					
VOH		I <sub>OH</sub> = -16 mA		0.1/	2.4			V	
		I <sub>OH</sub> = -24 mA		3 V	2.3				
_			4.5 V	3.8					
		I <sub>OL</sub> = 100 μA		1.65 V to 5.5 V			0.1		
VOL		I <sub>OL</sub> = 4 mA		1.65 V			0.45		
١.,		I <sub>OL</sub> = 8 mA		1.65 V to 5.5 V V <sub>CC</sub> -0.1  1.65 V 1.2  2.3 V 1.9  3 V 2.4  2.3  4.5 V 3.8  1.65 V to 5.5 V 0.1  1.65 V 0.45  2.3 V 0.45  2.3 V 0.45  2.3 V 0.45  2.5 V 0.55  4.5 V 0.55  4.5 V 0 to 5.5 V	.,				
$VOH \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$			0.4	V					
	I <sub>OL</sub> = 24 mA		3 V			0.55			
		I <sub>OL</sub> = 32 mA		4.5 V			0.55		
1.	A inputs	V <sub>I</sub> = 5.5 V or GND		0 to 5.5 V			±5	μΑ	
''	OE/OE inputs	V <sub>I</sub> = 5.5 V or GND		0 to 5.5 V			±5	μΑ	
l <sub>off</sub>		V <sub>I</sub> or V <sub>O</sub> = 5.5 V		0			±10	μΑ	
loz		V <sub>O</sub> = 0 to 5.5 V		3.6 V			10	μΑ	
1		V <sub>I</sub> = 5.5 V or GND	10	E E V			10		
'CC		$V_{I} = 3.6 \text{ V to } 5.5 \text{ V}^{\ddagger}$	1O = 0	5.5 V			0.45 0.3 0.4 0.55 0.55 ±5 ±10 10 10	μΑ	
Δlcc		One input at V <sub>CC</sub> – 0.6 V,	Other inputs at V <sub>CC</sub> or GND	3 V to 5.5 V	5.5 V 50		500	μΑ	
Ci		$V_I = V_{CC}$ or GND		3.3 V				pF	
Co		$V_O = V_{CC}$ or GND		3.3 V				pF	

<sup>†</sup> All typical values are at  $V_{CC}$  = 3.3 V,  $T_A$  = 25°C. ‡ This applies in the disabled state only.

## switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 4)

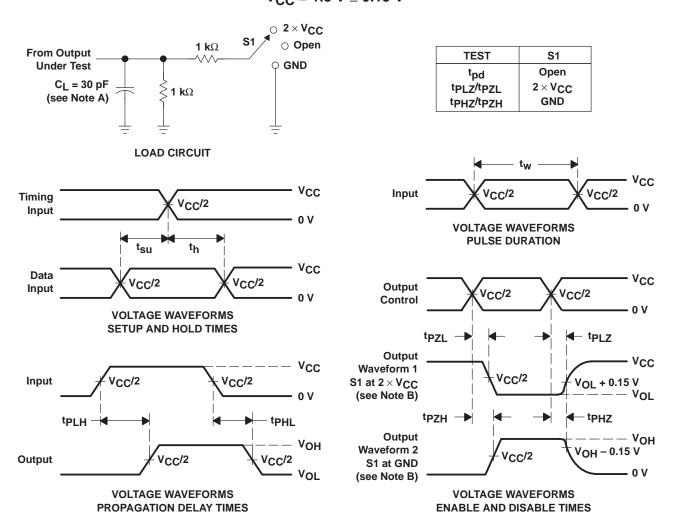
PARAMETER	FROM (INPUT)					V <sub>CC</sub> = 2.5 V ± 0.2 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		V <sub>CC</sub> = 5 V ± 0.5 V	
	(1141 01)	(0011 01)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
<sup>t</sup> pd	А	Υ									ns
t <sub>en</sub>	OE or OE	Υ									ns
<sup>t</sup> dis	OE or OE	Υ									ns

#### operating characteristics, T<sub>A</sub> = 25°C

PARAMETER		TEST	V <sub>CC</sub> = 1.8 V	V <sub>CC</sub> = 2.5 V	V <sub>CC</sub> = 3.3 V	V <sub>CC</sub> = 5 V	UNIT	
		CONDITIONS TYP	TYP	TYP	TYP	TYP	ONIT	
<u> </u>	Power dissipation capacitance	Outputs enabled	f = 10 MHz					pF
Cpd	per buffer/driver	Outputs disabled	1 = 10 MH2					рг



## PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$

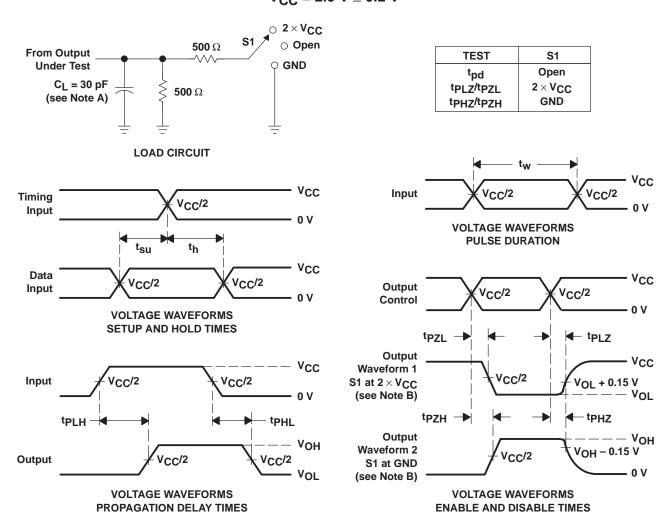


NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \Omega$ ,  $t_f \leq 2$  ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms

## PARAMETER MEASUREMENT INFORMATION $V_{CC}$ = 2.5 V $\pm$ 0.2 V

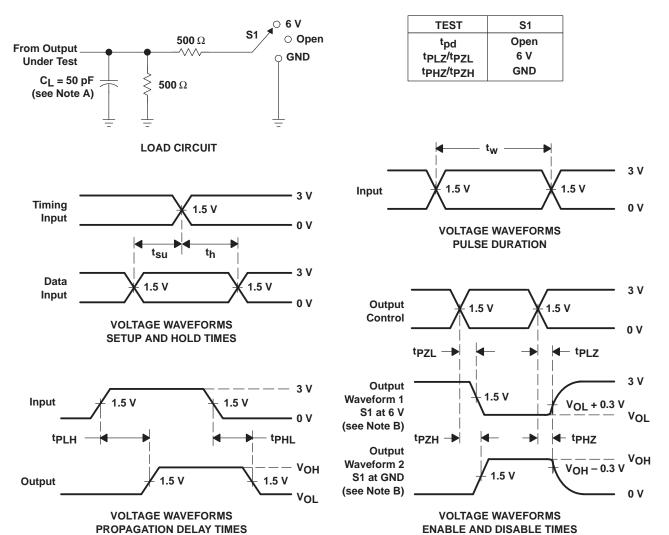


- NOTES: A. C<sub>L</sub> includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_Q = 50 \Omega$ ,  $t_f \leq 2$  ns.  $t_f \leq 2$  ns.
  - D. The outputs are measured one at a time with one transition per measurement.
  - E. tpLz and tpHz are the same as tdis.
  - F. tpzL and tpzH are the same as ten.
  - G. tpl H and tpHI are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms



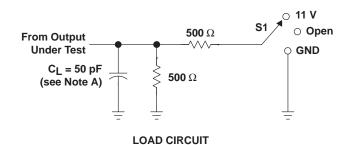
## PARAMETER MEASUREMENT INFORMATION $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$

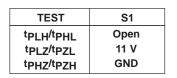


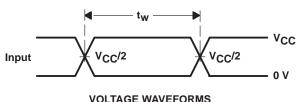
- NOTES: A.  $C_L$  includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_{O} = 50 \, \Omega$ ,  $t_{f} \leq 2.5 \, \text{ns}$ ,  $t_{f} \leq 2.5 \, \text{ns}$ .
  - D. The outputs are measured one at a time with one transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F. tpzL and tpzH are the same as ten.
  - G. tplH and tpHL are the same as tpd.

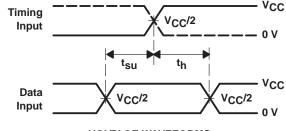
Figure 3. Load Circuit and Voltage Waveforms

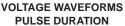
## PARAMETER MEASUREMENT INFORMATION $V_{CC}$ = 5 V $\pm$ 0.5 V

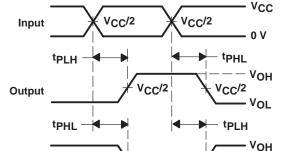






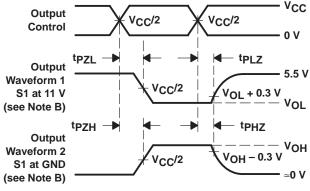






V<sub>CC</sub>/2

VOLTAGE WAVEFORMS SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS

VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C<sub>I</sub> includes probe and jig capacitance.

Output

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_Q = 50 \Omega$ ,  $t_f \leq 2.5 \text{ ns.}$
- D. The outputs are measured one at a time with one transition per measurement.

V<sub>CC</sub>/2

VOL

- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 4. Load Circuit and Voltage Waveforms



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